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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



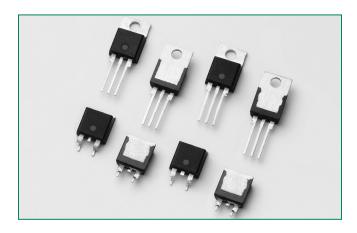






QJxx16xHx Series





Main Features

Symbol	Value	Unit
I _{T(RMS)}	16	А
V_{DRM}/V_{RRM}	400 or 600	V
I _{GT (Q1)}	10 to 80	mA

Description

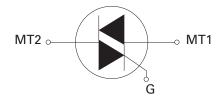
This 16A high temperature alternistor triac solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type components only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- Voltage capability up to 600V
- Surge capability up to 200A at 60Hz half cycle
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point in sine wave
- Requires only a short gate activation pulse in each half-cycle
- Halogen free and RoHS compliant

Schematic Symbol



Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with high inductive loads requiring the highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Thyristors16 Amp High Temperature Alternistor Triacs

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Paramete	Value	Unit		
		QJxx16LHy	T _c = 115 °C		
I _{T(RMS)}	RMS on-state current (full sine wave)	QJxx16RHy QJxx16NHy	T _C = 130 °C	16	А
1	Non repetitive surge peak on-state current	f = 50Hz	t = 20 ms	167	Α
TSM	(Single half cycle, T _J initial = 25°C)	f = 60Hz	t = 16.7 ms	200	A
l²t	l²t Value for fusing	166	A²s		
di/dt	Critical rate of rise of on-state current	f = 60Hz	T _J = 125 °C	100	A/µs
I _{GTM}	Peak gate trigger current	Peak gate trigger current $t_p \le 10 \mu s;$ $t_{gt} \le 1_{GTM}$		2.0	А
P _{G(AV)}	Average gate power dissipation	0.5	W		
T _{stg}	Storage temperature range	-40 to 150	°C		
T_{J}	Operating junction temperature range	-40 to 150	°C		
$V_{\rm DSM}/V_{\rm RSM}$	Peak non-repetitive blocking voltage	Pw=10	00 µs	$V_{DRM}/V_{RRM}+100$	V

xx = voltage/10, y = sensitivity

Electrical Characteristics (T_J = 25°C, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quad	rant	QJxx16xH2	QJx16xH3	QJx16xH4	QJx16xH6	Unit
I _{GT}	V 12V B 600	1 – 11 – 111	MAX.	10	20	35	80	mA
$V_{\rm GT}$	$V_D = 12V R_L = 60\Omega$	1 – 11 – 111	MAX.		1.:	3		V
V_{GD}	$V_D = V_{DRM} R_L = 3.3 k\Omega T_J = 150$ °C	1 – 11 – 111	MIN.	0.15			V	
I _H	I _T = 100mA		MAX.	15	35	50	70	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 150$ °C 600V		MIN.	-	250	350	850	\//u0
uv/ut	$V_D = 2/3 V_{DRM}$ Gate Open $T_J = 150$ °C		MIN.	50	300	400	925	V/µs
(dv/dt)c	$(di/dt)c = 8.6 \text{ A/ms T}_J = 150^{\circ}\text{C}$		MIN.	2	20	25	30	V/µs
t _{gt}	$I_{G} = 2 \times I_{GT} \text{ PW} = 15 \mu \text{s} I_{T} = 22.6 \text{ A(pk)}$		TYP.	3	3	3	5	μs

Static Characteristics

Symbol	Test	Value	Unit		
V _{TM}	$I_{T} = 22.6A t_{p} = 3$	$I_{T} = 22.6A t_{p} = 380 \mu s$			V
1 /1	@\\\\\	T _J = 25°C	MAX	5	μA
I _{DRM} / I _{RRM}	I_{DRM}/I_{RRM} @ V_{DRM}/V_{RRM}	T _J = 150°C		4	mA

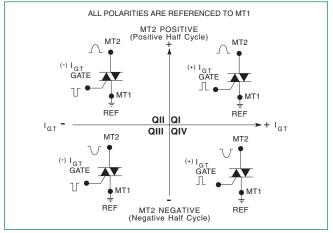
Thermal Resistances

Symbol	Parameter	Value	Unit		
R	Junction to case (AC)	QJxx16RHy QJxx16NHy	0.90	°C/W	
$R_{\theta(J-C)}$		QJxx16LHy	1.8	5,00	
R Junction to ambient		QJxx16RHy QJxx16NHy	45	°C/W	
$R_{\theta(J-A)}$	Sunction to unidiont	QJxx16LHy	50		

xx = voltage/10; y = sensitivity



Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 3: Normalized DC Holding Current vs. Junction Temperature

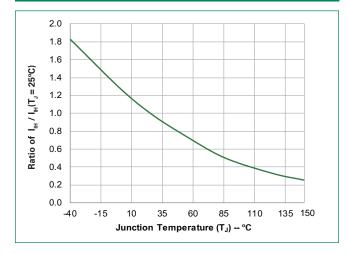


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

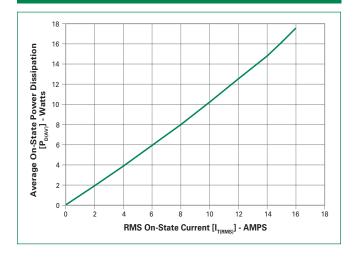


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

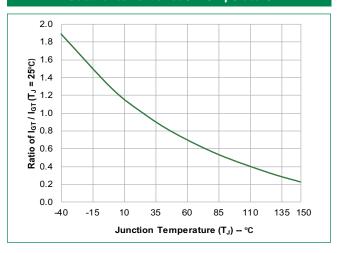


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

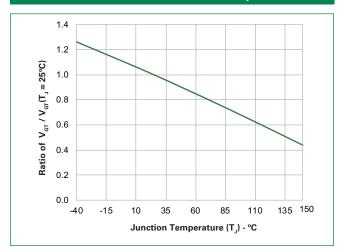


Figure 6: On-State Current vs. On-State Voltage (Typical)

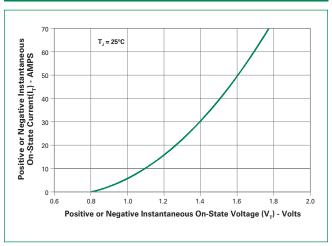




Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

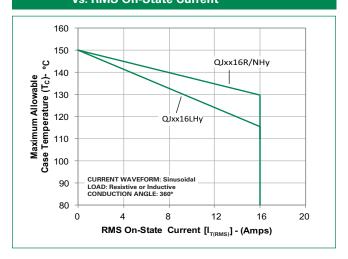
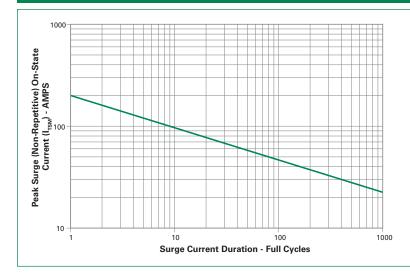


Figure 9: Surge Peak On-State Current vs. Number of Cycles



Supply Frequency: 60Hz Sinusoidal

Load: Resistive

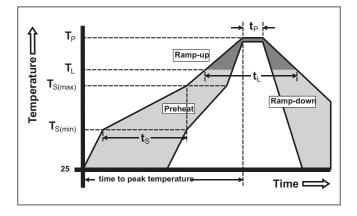
RMS On-State [$I_{T(RMS)}$]: Max Rated Value at Specific Case Temperature

Notes:

- Gate control may be lost during and immediately following surge current interval.
- Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Co	ndition	Pb – Free assembly	
	-Temperature Min (T _{s(min)})	150°C	
Pre Heat	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ra	amp up rate (LiquidusTemp) k	5°C/second max	
T _{S(max)} to T _L	- Ramp-up Rate	5°C/second max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
nellow	-Time (t _L)	60 – 150 seconds	
PeakTemp	erature (T _P)	260 ^{+0/-5} °C	
Time with Temperatu	in 5°C of actual peak ure (t _p)	20 – 40 seconds	
Ramp-dov	vn Rate	5°C/second max	
Time 25°C to peakTemperature (T _p)		8 minutes Max.	
Do not exc	ceed	280°C	



Thyristors16 Amp High Temperature Alternistor Triacs

Physical Specifications

Terminal Finish	100% Matte Tin-plated	
Body Material	UL Recognized epoxy meeting flammability rating V-0	
Terminal Material	Copper Alloy	

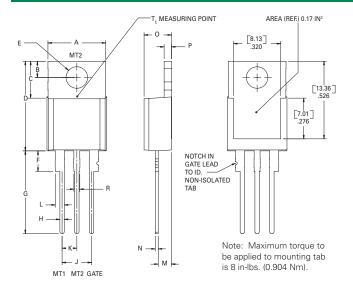
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/ Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E
Moisture Sensitivity Level	Level 1, JEDEC-J-STD-020

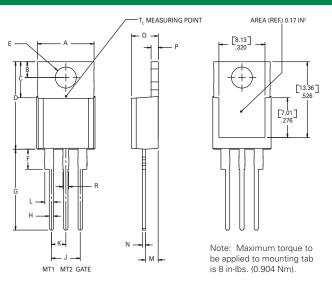
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inc	hes	Millimeters		
Dimension	Min	Max	Min	Max	
А	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.66	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
Е	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.61	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
K	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
М	0.085	0.095	2.16	2.41	
N	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
Р	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

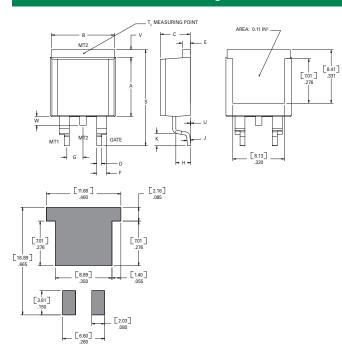


Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Incl	nes	Millimeters		
Dimension	Min	Max	Min	Max	
А	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.67	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
Е	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.60	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
K	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
М	0.085	0.095	2.16	2.41	
N	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
Р	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

Dimensions — TO-263AB (N-Package) — D²Pak Surface Mount



Dimension	Incl	nes	Millimeters		
Dimension	Min	Max	Min	Max	
А	0.360	0.370	9.14	9.40	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
Е	0.045	0.060	1.14	1.52	
F	0.060	0.075	1.52	1.91	
G	0.095	0.105	2.41	2.67	
Н	0.092	0.102	2.34	2.59	
J	0.018	0.024	0.46	0.61	
K	0.090	0.110	2.29	2.79	
S	0.590	0.625	14.99	15.88	
V	0.035	0.045	0.89	1.14	
U	0.002	0.010	0.05	0.25	
W	0.040	0.070	1.02	1.78	

Thyristors16 Amp High Temperature Alternistor Triacs

Product Selector

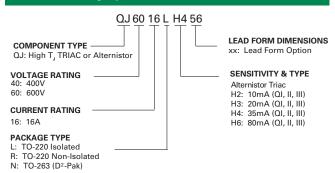
David November	Vol	tage	Gate Sensitivity Quadrants	T	Deales as
Part Number	400V	600V	I – II – III	Type	Package
QJxx16LH2	Х	Х	10 mA	Alternistor Triac	TO-220L
QJxx16RH2	X	X	10 mA	Alternistor Triac	TO-220R
QJxx16NH2	X	X	10 mA	Alternistor Triac	TO-263 D²-PAK
QJxx16LH3	X	X	20 mA	Alternistor Triac	TO-220L
QJxx16RH3	Х	Х	20 mA	Alternistor Triac	TO-220R
QJxx16NH3	Х	Х	20 mA	Alternistor Triac	TO-263 D²-PAK
QJxx16LH4	X	X	35 mA	Alternistor Triac	TO-220L
QJxx16RH4	X	X	35 mA	Alternistor Triac	TO-220R
QJxx16NH4	Х	X	35 mA	Alternistor Triac	TO-263 D²-PAK
QJxx16LH6	Х	Х	80 mA	Alternistor Triac	TO-220L
QJxx16RH6	Х	X	80 mA	Alternistor Triac	TO-220R
QJxx16NH6	Х	Х	80 mA	Alternistor Triac	TO-263 D²-PAK

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
QJxx16L/RHyTP	QJxx16L/RHy	2.2 g	Tube Pack	500 (50 per tube)
QJxx16NHyTP	QJxx16NHy	1.6 g	Tube Pack	500 (50 per tube)
QJxx16NHyRP	QJxx16NHy	1.6 g	Embossed Carrier	500

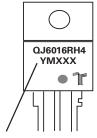
xx = voltage/10; y = Sensitivity

Part Numbering System



Part Marking System

TO-220 AB - (L and R Package) TO-263 AB - (N Package)

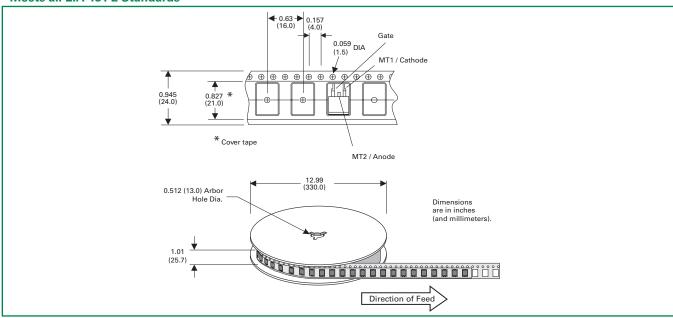


Date Code Marking Y:Year Code M: Month Code XXX: LotTrace Code



TO-263 Embossed Carrier Reel Pack (RP)

Meets all EIA-481-2 Standards



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